## 2SD468

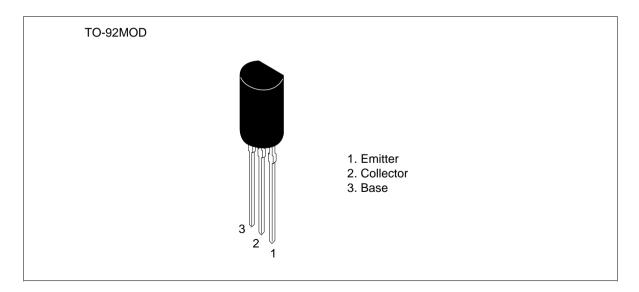
## Silicon NPN Epitaxial

# **HITACHI**

### **Application**

- Low frequency power amplifier
- Complementary pair with 2SB562

#### Outline





### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	25	V
Collector to emitter voltage	V <sub>CEO</sub>	20	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	I <sub>c</sub>	1.0	A
Collector peak current	i <sub>C(peak)</sub>	1.5	A
Collector power dissipation	P <sub>c</sub>	0.9	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

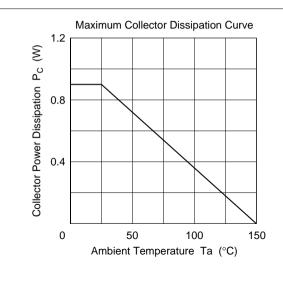
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

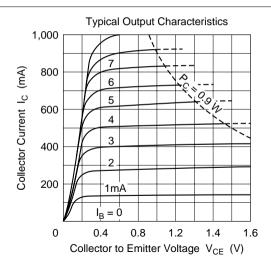
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1.0	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	85	_	240		$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.2	0.5	V	$I_C = 0.8 \text{ A}, I_B = 0.08 \text{ A}^{*2}$
Base to emitter voltage	$V_{BE}$	_	0.79	1.0	V	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}^{*2}$
Gain bandwidth product	f <sub>T</sub>	_	190	_	MHz	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}^{*2}$
Collector output capacitance	Cob	_	22	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

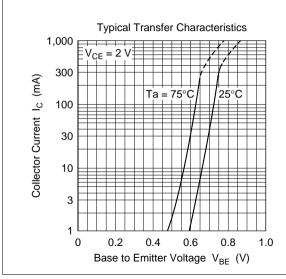
Notes: 1. The 2SD468 is grouped by h<sub>FE</sub> as follows.

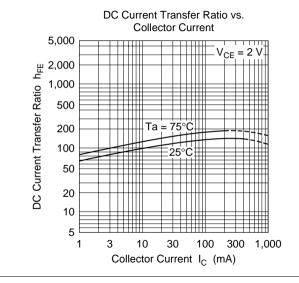
2. Pulse test

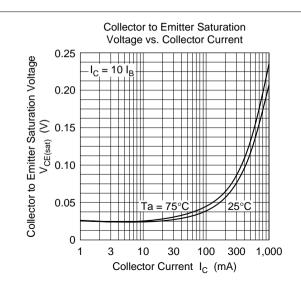
В	С
85 to170	120 to 240

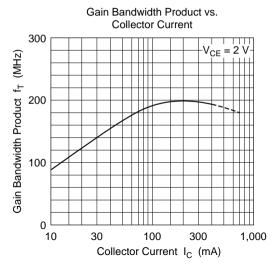


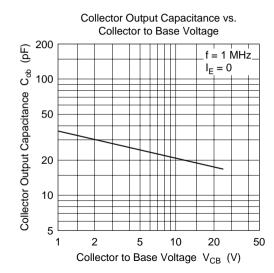




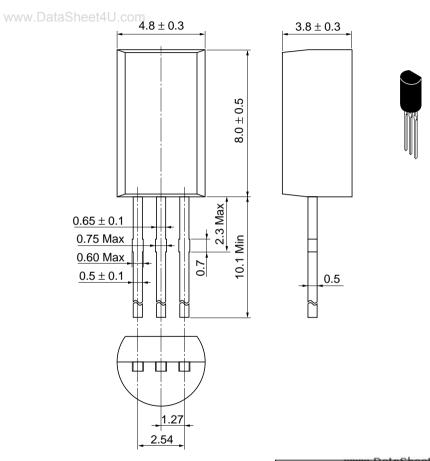








Unit: mm



Hitachi Code WWW.Data	TO-92 Mod
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.35 g

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